

ABSTRACT

DOUBLE SIDED CONTAINER CAPACITOR FOR A SEMICONDUCTOR DEVICE AND METHOD FOR FORMING SAME

A method for forming a double sided container capacitor comprises forming a first capacitor top plate layer within a recess in a dielectric layer, then forming a first cell dielectric on the first top plate layer. Next, first and second bottom plate layers are formed on the first cell dielectric layer, and a second cell dielectric layer is formed on the second bottom plate layers. Finally, a second top plate layer is formed on the second cell dielectric layer, and the first and second top plate layers are electrically connected using a conductive plug or conductive spacer. An inventive structure formed using the inventive method is also described.